ASSP

Spread Spectrum Clock Generator

MB88151A

DESCRIPTION

MB88151A is a clock generator for EMI (Electro Magnetic Interference) reduction. The peak of unnecessary radiation noise (EMI) can be attenuated by making the oscillation frequency slightly modulate periodically with the internal modulator. It corresponds to both of the center spread which modulates frequency in modulation off as Middle Centered and down spread which modulates so as not to exceed frequency in modulation off.

FEATURES

	MB88151A- 100/101 (multiply-by-1)	MB88151A- 200/201 (multiply-by-2)	MB88151A- 400/401 (multiply-by-4)	MB88151A- 500/501 (multiply-by-1/2)	MB88151A- 800/801 (multiply-by-8)	
Input frequency/ Output frequency	16.6 MHz to 33.4 MHz/ 16.6 MHz to 33.4 MHz	16.6 MHz to 33.4 MHz/ 33.2 MHz to 66.8 MHz	16.6 MHz to 33.4 MHz/ 66.4 MHz to 133.6 MHz	16.6 MHz to 33.4 MHz/ 8.3 MHz to 16.7 MHz	8.3 MHz to 16.7 MHz 66.4 MHz to 133.6 MHz	
Modulation clock cycle-cycle jitter	Less than100 ps	Less than 100 ps	Less than 150 ps	Less than 200 ps	Less than 150 ps	

• Modulation rate : $\pm 0.5\%$, $\pm 1.5\%$ (Center spread), -1.0%, -3.0% (Down spread)

- Equipped with oscillation circuit : Range of oscillation 8.3 MHz to 33.4 MHz
- Modulation clock output Duty : 40% to 60%
- Low current consumption by CMOS process : 5 mA (24 MHz : Typ-sample, no load)
- Power supply voltage : 3.3 V \pm 0.3 V
- Operating temperature : 40 °C to + 85 °C
- Package : SOP 8-pin

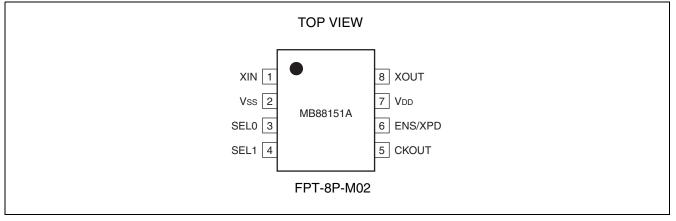


■ PRODUCT LINEUP

MB88151A has five kinds of multiplication type.

Product	Input frequency range	Multiplier ratio	Output frequency range
MB88151A-100/101		Multiply-by-1	16.6 MHz to 33.4 MHz
MB88151A-200/201	16.6 MHz to 33.4 MHz	Multiply-by-2	33.2 MHz to 66.8 MHz
MB88151A-400/401		Multiply-by-4	66.4 MHz to 133.6 MHz
MB88151A-500/501		Multiply-by-1/2	8.3 MHz to 16.7 MHz
MB88151A-800/801	8.3 MHz to 16.7 MHz	Multiply-by-8	66.4 MHz to 133.6 MHz

■ PIN ASSIGNMENT

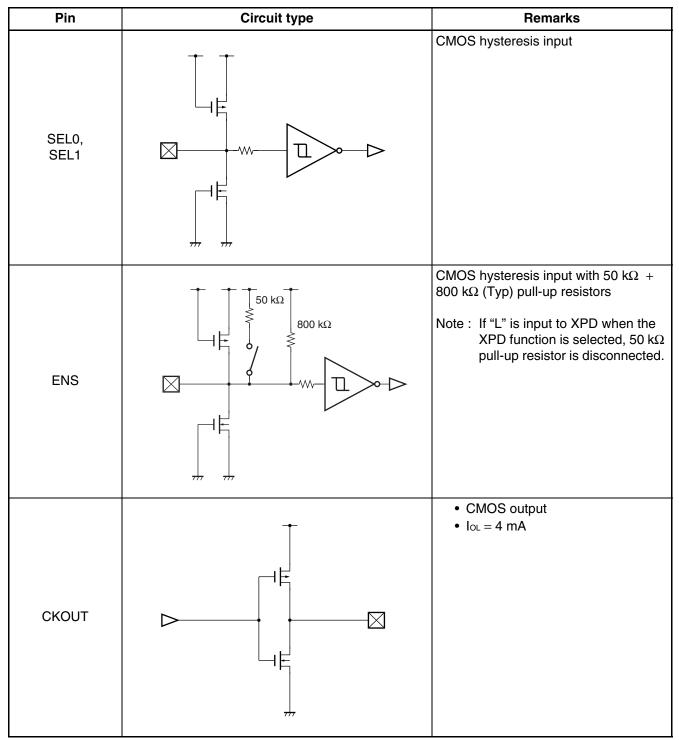


■ PIN DESCRIPTION

Pin name	I/O	Pin no.	Description
XIN	I	1	Resonator connection pin/clock input pin
Vss		2	GND pin
SEL0	I	3	Modulation rate setting pin
SEL1	I	4	Modulation rate setting pin
CKOUT	0	5	Modulated clock output pin
ENS/XPD	I	6	Modulation enable setting pin (with pull-up resistance)/ Power down pin (with pull-up resistor)*
Vdd	—	7	Power supply voltage pin
XOUT	0	8	Resonator connection pin

* : XPD = 800 k Ω pull-up resistor at "L"

■ I/O CIRCUIT TYPE



Note : For XIN and XOUT pins, refer to "■OSCILLATION CIRCUIT".

HANDLING DEVICES

Preventing Latch-up

A latch-up can occur if, on this device, (a) a voltage higher than V_{DD} or a voltage lower than V_{SS} is applied to an input or output pin or (b) a voltage higher than the rating is applied between V_{DD} pin and V_{SS} pin. The latch-up, if it occurs, significantly increases the power supply current and may cause thermal destruction of an element. When you use this device, be very careful not to exceed the maximum rating.

Handling unused pins

Do not leave an unused input pin open, since it may cause a malfunction. Handle by, using a pull-up or pull-down resistor.

Unused output pin should be opened.

The attention when the external clock is used

Input the clock to XIN pin, and XOUT pin should be opened when you use the external clock. Please pay attention so that an overshoot and an undershoot do not occur to an input clock of XIN pin.

Power supply pins

Please design connecting the power supply pin of this device by as low impedance as possible from the current supply source.

We recommend connecting electrolytic capacitor (about 10 μ F) and the ceramic capacitor (about 0.01 μ F) in parallel between Vss pin and VDD pin near the device, as a bypass capacitor.

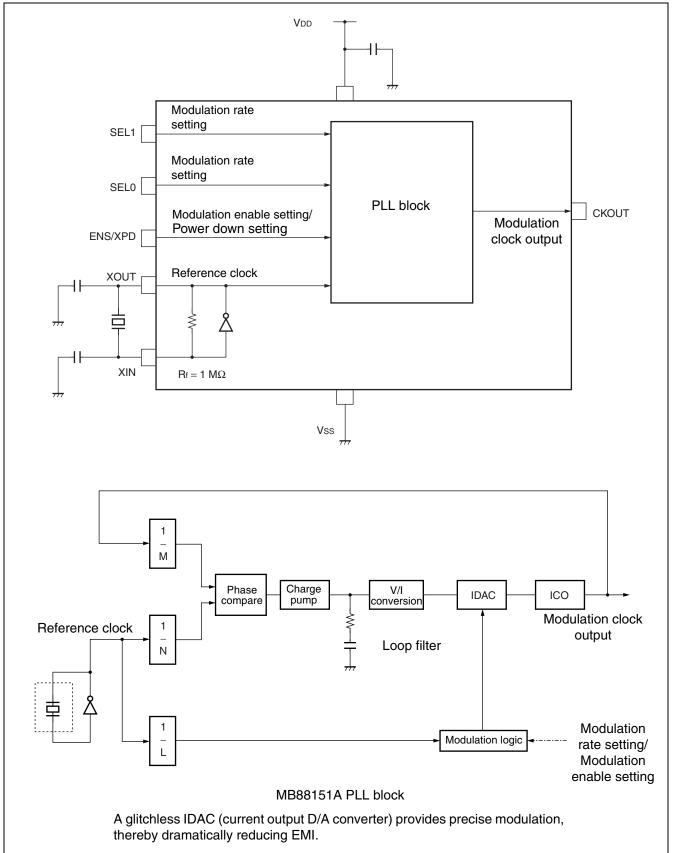
Oscillation circuit

Noise near the XIN and XOUT pins may cause the device to malfunction. Design printed circuit boards so that electric wiring of XIN or XOUT pin and the resonator do not intersect other wiring.

Design the printed circuit board that surrounds the XIN and XOUT pins with ground.

MB88151A

■ BLOCK DIAGRAM



■ PIN SETTING

When changing the pin setting, the stabilization wait time for the modulation clock is required. The stabilization wait time for the modulation clock take the maximum value of "■ ELECTRICAL CHARACTERISTICS • AC Characteristics Lock-up time".

ENS modulation enable setting (MB88151A-100/200/400/500/800)

ENS	Modulation
L	No modulation
Н	Modulation

Note : Spectrum does not spread when "L" is set to ENS. The clock with low jitter can be obtained. Because of ENS has Pull-up resistance, spectrum spread when "H" is set to it or open the terminal.

XPD Power down setting (MB88151A-101/201/401/501/801)

XPD	Status
L	Power down Status
Н	Operating status

Note : CKOUT of output pins are fixed to "L" output during power down.

SEL0, SEL1 Modulation rate setting

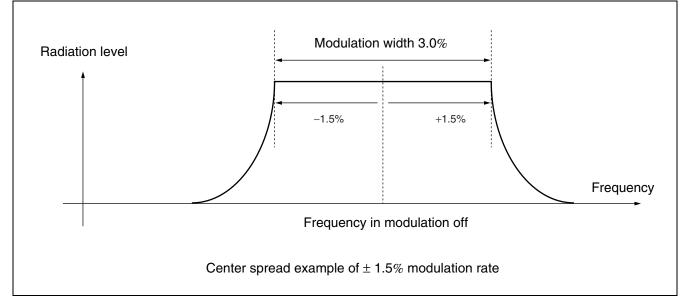
SEL1	SEL0	Modulation rate	Modulation type
L	L	± 1.5%	Center spread
L	н	± 0.5%	Center spread
Н	L	- 1.0%	Down spread
Н	Н	- 3.0%	Down spread

Note : The modulation rate can be changed at the level of the terminal.

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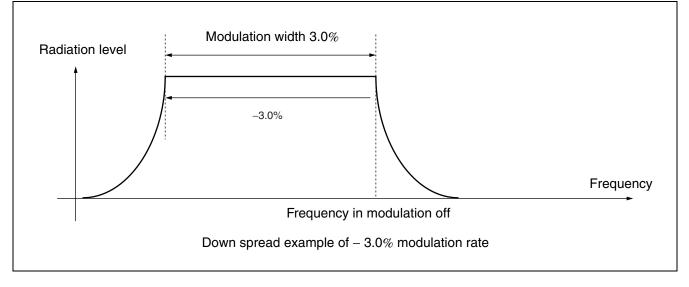
• Center spread

Spectrum is spread (modulated) by centering on the frequency in modulation off.



• Down spread

Spectrum is spread (modulated) below the frequency in modulation off.

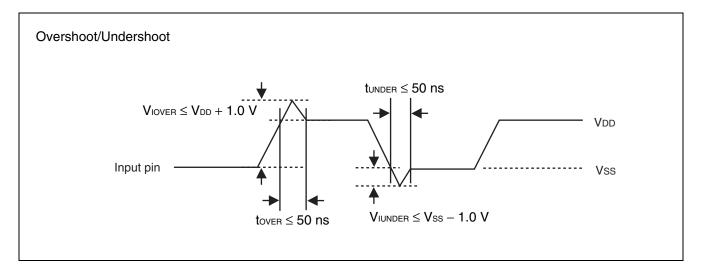


■ ABSOLUTE MAXIMUM RATINGS

Devementer	Cumbal	Rating			
Parameter	Symbol	Min	Мах	- Unit	
Power supply voltage*	Vdd	- 0.5	+ 4.0	V	
Input voltage*	V	Vss - 0.5	V _{DD} + 0.5	V	
Output voltage*	Vo	Vss - 0.5	V _{DD} + 0.5	V	
Storage temperature	Тsт	- 55	+ 125	°C	
Operation junction temperature	TJ	- 40	+ 125	°C	
Output current	lo	- 14	+ 14	mA	
Overshoot	VIOVER	—	V_{DD} + 1.0 (tover \leq 50 ns)	V	
Undershoot	VIUNDER	Vss-1.0 (tunder \leq 50 ns)		V	

* : The parameter is based on $V_{SS} = 0.0 V$.

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.



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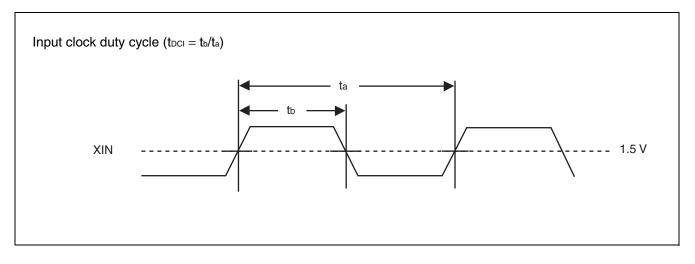
RECOMMENDED OPERATING CONDITIONS

			T			(V	ss = 0.0 V)
Parameter	Symbol	Pin	n Conditions		Value		Unit
Faiaillelei	Symbol	FIII	Conditions	Min	Тур	Max	Onit
Power supply voltage	Vdd	Vdd		3.0	3.3	3.6	V
"H" level input voltage	VIH	XIN,		$V_{\text{DD}} imes 0.8$	_	V _{DD} + 0.3	V
"L" level input voltage	VIL	SEL0, SEL1, ENS		Vss		$V_{\text{DD}} imes 0.2$	V
Input clock duty cycle	tDCI	XIN	8.3 MHz to 33.4 MHz	40	50	60	%
Operating temperature	Та			- 40	_	+ 85	°C

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.



■ ELECTRICAL CHARACTERISTICS

• DC Characteristics

(Ta = - 40 $^{\circ}C$ to ~+ 85 $^{\circ}C,~V_{\text{DD}}$ = 3.3 V \pm 0.3 V, Vss = 0.0 V)

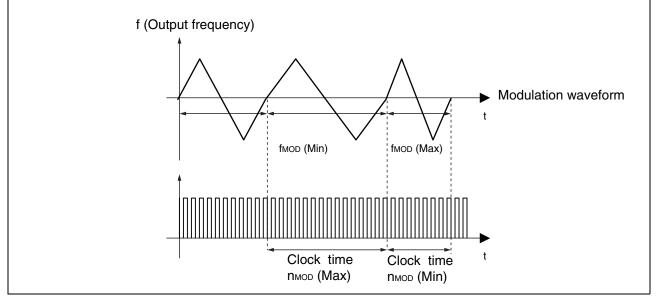
Parameter	Symbol Pin		Conditions		Unit			
Parameter	Symbol	Pin	Conditions	Min	Тур	Max		
Power supply current	lcc	VDD	No load capacitance at output 24 MHz MB88151A-100	_	5.0	7.0	mA	
			At power down MB88151A-101	_	10	_	μA	
Output voltage	Vон	CKOUT	"H" level output, Іон = – 4 mA	$V_{\text{DD}}-0.5$		Vdd	V	
	Vol	CKOUT	"L" level output, Io∟ = 4 mA	Vss		0.4	V	
Output impedance	Zo	CKOUT	8.3 MHz to 133.6 MHz	—	45	—	Ω	
Input capacitance	Cin	XIN, SEL0, SEL1, ENS	$Ta = +25 \ ^{\circ}C,$ $V_{DD} = V_{I} = 0.0 \ V,$ $f = 1 \ MHz$		_	16	pF	
			8.3 MHz to 66.8 MHz	—		15		
Load capacitance	CL	CKOUT	66.8 MHz to 100 MHz	—		10	pF	
			100 MHz to 133.6 MHz			7		
Input pull-up resistance	RPUE	ENS	$V_{\text{IL}}=0.0~V$	25	50	200	kO	
	Rpup	XPD	$V_{\text{IL}}=0.0~V$	500	800	1200	– kΩ	

• AC Characteristics

Paramatar	Symbol	Pin	Conditions		Value		Unit	
Parameter	Symbol	Pin	Conditions	Min	Тур	Max	Unit	
Oscillation frequency	fx	XIN, XOUT	Fundamental oscillation	8.3		33.4	MHz	
Input frequency	fin	XIN	External clock input (multiply-by-1, 2, 4, divided by 2)	16.6		33.4	MHz	
			External clock input (multiply-by-8)	8.3		16.7		
			MB88151A-100/101 (Multiply by 1)	16.6	_	33.4		
			MB88151A-200/201 (Multiply by 2)	33.2	_	66.8		
Output frequency	fouт	СКОИТ	MB88151A-400/401 (Multiply by 4)	66.4	_	133.6	MHz	
			MB88151A-500/501 (2-frequency division)	8.3		16.7		
			MB88151A-800/801 (multiply-by-8)	66.4		133.6		
Output slew rate	SR	CKOUT	0.4 V to 2.4 V Load capacitance 15 pF	0.4	_	4.0	V/ns	
Output clock duty cycle	tDCC	CKOUT	1.5 V	40	_	60	%	
Modulation period (Number of input clocks per modulation)	fмор (пмор)	СКОПТ	MB88151A-100/101, MB88151A-200/201, MB88151A-400/401, MB88151A-500/501	fin/2200 (2200)	fin/1900 (1900)	fin/1600 (1600)	kHz (clks)	
per modulation)			MB88151A-800/801	fin/880 (880)	fin/760 (760)	fin/640 (640)	kHz (clks)	
Lock-up time	t∟ĸ	СКОИТ	8.3 MHz to 80 MHz	_	2	5	me	
Lock-up time	LK	CROOT	80 MHz to 133.6 MHz	_	3	8	ms	
	cle jitter tuc CKC		MB88151A-100/101, MB88151A-200/201 No load capacitance, Ta = $+25 \degree$ C, V _{DD} = 3.3 V	_	_	100		
Cycle-cycle jitter			MB88151A-400/401, MB88151A-800/801 No load capacitance, Ta = + 25 °C, V _{DD} = 3.3 V			150	ps-rms	
			$\begin{array}{l} \text{MB88151A-500/501}\\ \text{No load capacitance,}\\ \text{Ta}=+25\ ^\circ\text{C},\ \text{V}_{\text{DD}}=3.3\ \text{V} \end{array}$			200		

(Ta = - 40 $^{\circ}C$ to ~+ 85 $^{\circ}C,~V_{\text{DD}}$ = 3.3 V \pm 0.3 V, Vss = 0.0 V)

Note : The modulation clock stabilization wait time is required after the power is turned on, the IC recovers from power saving, or after FREQ (frequency range) or ENS (modulation ON/OFF) setting is changed. For the modulation clock stabilization wait time, assign the maximum value for lock-up time.



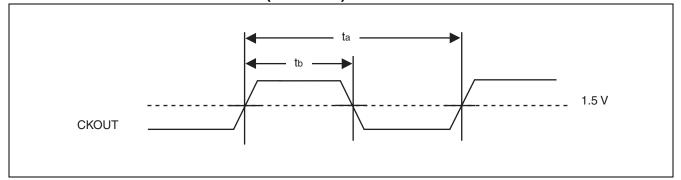
<Definition of modulation frequency and number of input clocks per modulation>

MB88151A contains the modulation period to realize the efficient EMI reduction.

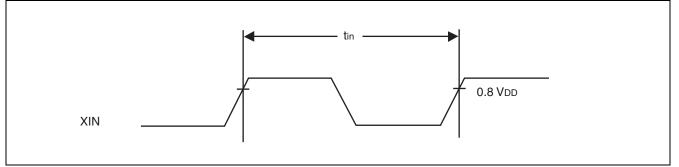
The modulation period f_{MOD} depends on the input frequency and changes between f_{MOD} (Min) and f_{MOD} (Max). Furthermore, the average value of f_{MOD} equals the typical value of the electrical characteristics.

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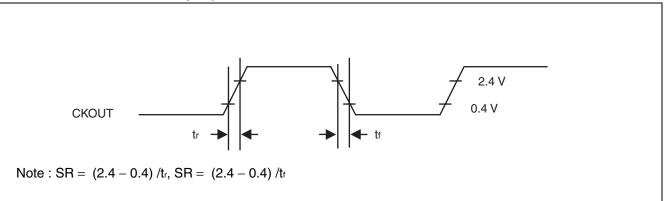
■ OUTPUT CLOCK DUTY CYCLE (t_{DCC} = t_b/t_a)



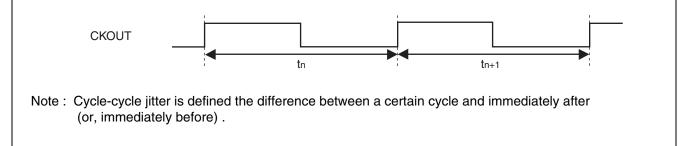
■ INPUT FREQUENCY (fin = 1/tin)



■ OUTPUT SLEW RATE (SR)

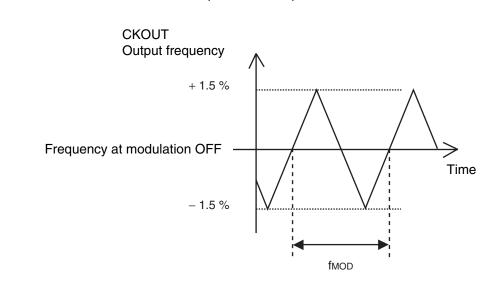


■ CYCLE-CYCLE JITTER (t_{JC} = | t_n - t_{n+1} |)

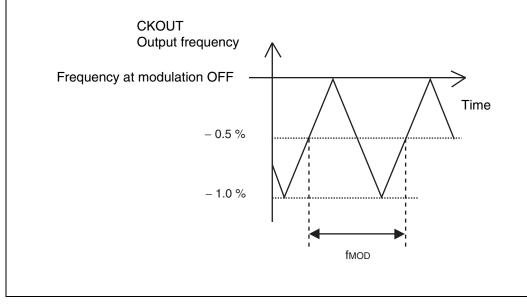


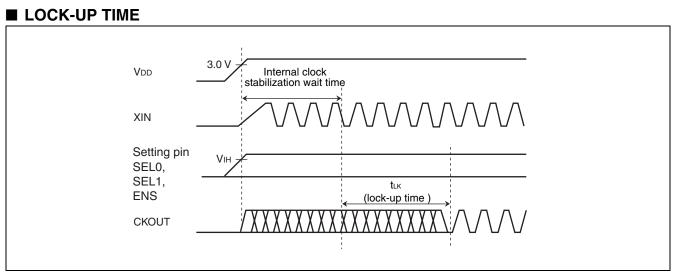
■ MODULATION WAVEFORM

• $\pm 1.5\%$ modulation rate, Example of center spread

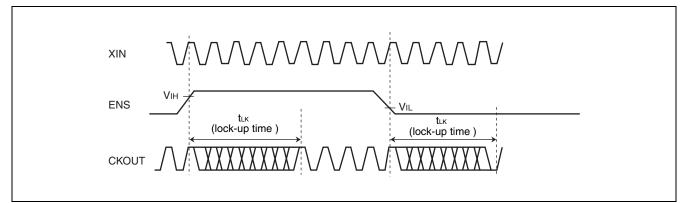


• -1.0% modulation rate, Example of down spread



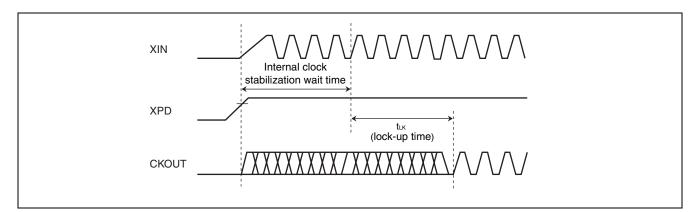


If the setting pin is fixed at the "H" or "L" level, the maximum time after the power is turned on until the set clock signal is output from CKOUT pin is (the stabilization wait time of input clock to XIN pin) + (the lock-up time "tLK"). For the input clock stabilization time, check the characteristics of the resonator or oscillator used.



For modulation enable control using the ENS pin during normal operation, the set clock signal is output from CKOUT pin at most the lock-up time (t_{LK}) after the level at the ENS pin is determined.

Note : When the pin setting is changed, the CKOUT pin output clock stabilization time is required. Until the output clock signal becomes stable, the output frequency, output clock duty cycle, modulation period, and cycle-cycle jitter cannot be guaranteed. It is therefore advisable to perform processing such as cancelling a reset of the device at the succeeding stage after the lock-up time.



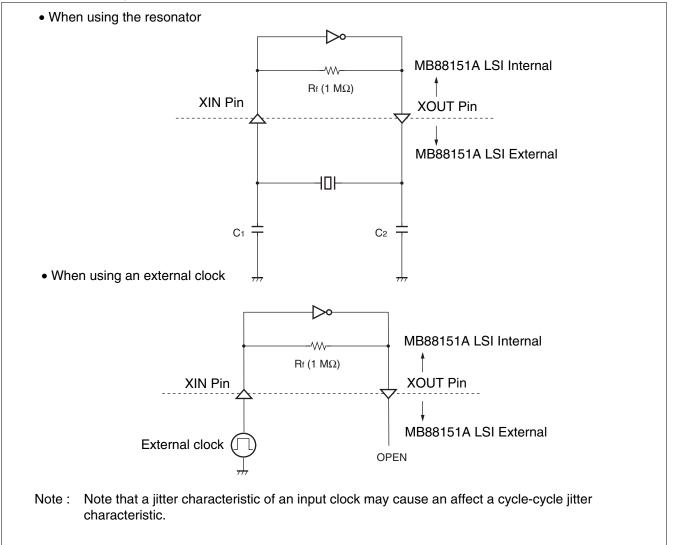
When the power down is controlled by XPD pin, the desired clock is obtained after the pin is set to H level until the maximum lock-up time tLk is elapsed.

OSCILLATION CIRCUIT

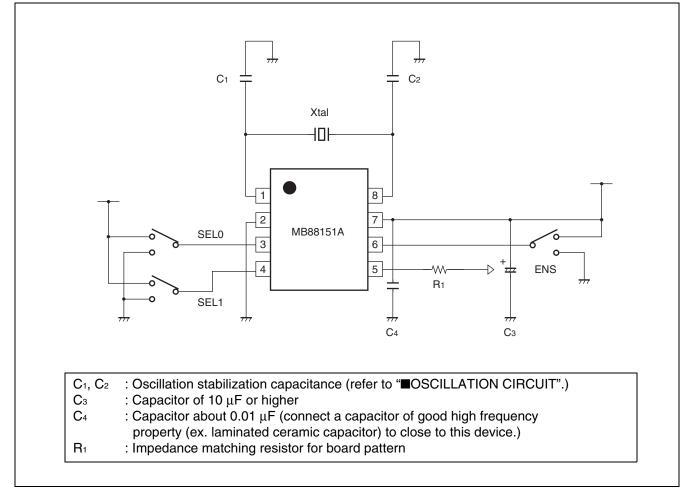
The figure below shows the connection example about general resonator. The oscillation circuit has the built-in resistance $(1 \text{ M}\Omega)$. The value of capacity (C₁ and C₂) is required adjusting to the most suitable value of individual resonator.

The most suitable value is different by individual resonator. Please refer to the resonator manufacturer which you use for the most suitable value.

Input the clock to XIN pin, and do not connect anything with XOUT pin if you use the external clock (you do not use the resonator).



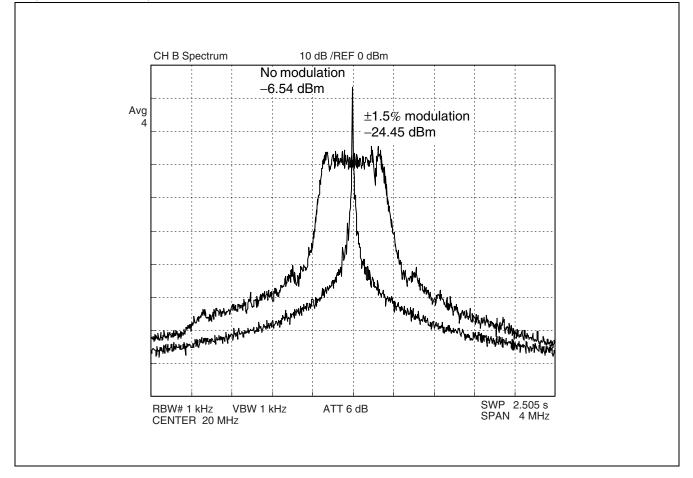
■ INTERCONNECTION CIRCUIT EXAMPLE



SPECTRUM EXAMPLE CHARACTERISTICS

The condition of the examples of the characteristic is shown as follows : Input frequency = 20 MHz (Output frequency = 20 MHz : Using MB88151A-100 (Multiply-by-1)), Power - supply voltage = 3.3 V, None load capacity, Modulation rate = $\pm 1.5\%$ (center spread).

Spectrum analyzer HP4396B is connected with CKOUT. The result of the measurement with RBW = 1 kHz (ATT use for -6dB).

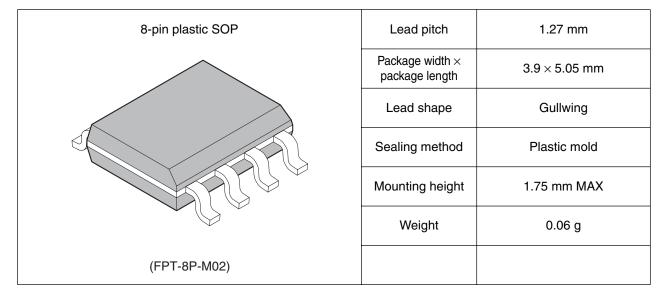


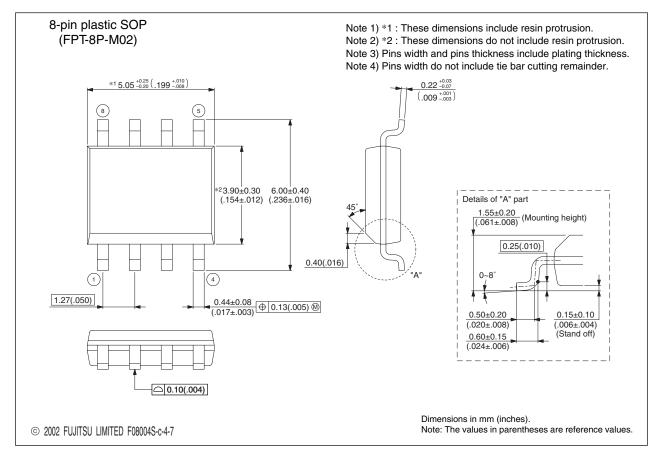
■ ORDERING INFORMATION

Part number	Input frequency range	Multiplier ratio	Output frequency range	Package	Remarks
MB88151APNF-G-100-JNE1 MB88151APNF-G-101-JNE1		Multiply- by-1	16.6 MHz to 33.4 MHz		
MB88151APNF-G-200-JNE1 MB88151APNF-G-201-JNE1	16.6 MHz to	Multiply- by-2	33.2 MHz to 66.8 MHz		
MB88151APNF-G-400-JNE1 MB88151APNF-G-401-JNE1	33.4 MHz	Multiply- by-4	66.4 MHz to 133.6 MHz		
MB88151APNF-G-500-JNE1 MB88151APNF-G-501-JNE1		Multiply- by-1/2	8.3 MHz to 16.7 MHz		
MB88151APNF-G-800-JNE1 MB88151APNF-G-801-JNE1	8.3 MHz to 16.7 MHz	Multiply- by-8	66.4 MHz to 133.6 MHz		
MB88151APNF-G-100-JNEFE1 MB88151APNF-G-101-JNEFE1	16.6 MHz to 33.4 MHz	Multiply- by-1	16.6 MHz to 33.4 MHz	8-pin plastic SOP (FPT-8P-M02)	
MB88151APNF-G-200-JNEFE1 MB88151APNF-G-201-JNEFE1		Multiply- by-2	33.2 MHz to 66.8 MHz		Emboss taping (EF type)
MB88151APNF-G-400-JNEFE1 MB88151APNF-G-401-JNEFE1		Multiply- by-4	66.4 MHz to 133.6 MHz		
MB88151APNF-G-500-JNEFE1 MB88151APNF-G-501-JNEFE1		Multiply- by-1/2	8.3 MHz to 16.7 MHz		
MB88151APNF-G-800-JNEFE1 MB88151APNF-G-801-JNEFE1	8.3 MHz to 16.7 MHz	Multiply- by-8	66.4 MHz to 133.6 MHz		
MB88151APNF-G-100-JNERE1 MB88151APNF-G-101-JNERE1		Multiply- by-1	16.6 MHz to 33.4 MHz		
MB88151APNF-G-200-JNERE1 MB88151APNF-G-201-JNERE1	16.6 MHz to	Multiply- by-2	33.2 MHz to 66.8 MHz		
MB88151APNF-G-400-JNERE1 MB88151APNF-G-401-JNERE1	33.4 MHz	Multiply- by-4	66.4 MHz to 133.6 MHz		Emboss taping (ER type)
MB88151APNF-G-500-JNERE1 MB88151APNF-G-501-JNERE1		Multiply- by-1/2	8.3 MHz to 16.7 MHz		
MB88151APNF-G-800-JNERE1 MB88151APNF-G-801-JNERE1	8.3 MHz to 16.7 MHz	Multiply- by-8	66.4 MHz to 133.6 MHz		

MB88151A

■ PACKAGE DIMENSION





Please confirm the latest Package dimension by following URL. http://edevice.fujitsu.com/fj/DATASHEET/ef-ovpklv.html

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